

DO NOT ENTER: /JC/ (01/27/2009)

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

forming an interlayer insulator comprising at least an upper layer comprising silicon nitride and a lower layer comprising silicon oxide, each comprising different dry etching characteristics;

etching the upper layer of the interlayer insulator using a first mask, wherein the lower layer of the interlayer insulator is used as an etching stopper;

forming a second mask to cover a portion of the lower layer of the interlayer insulator, which is exposed by the etching step; and

selectively etching the lower layer of the interlayer insulator using the second mask to form a contact hole,

wherein the second mask is different from the first mask.

2. (Previously Presented) A method for manufacturing a semiconductor device comprising at least one thin film transistor, comprising the steps of:

forming a first conductive film on a gate insulating film;

patterning the first conductive film to form a gate electrode;

forming an interlayer insulator comprising at least two layers on the gate insulating film;

forming a first contact hole by removing a part of an upper layer of the interlayer insulator, the part being located over at least one of a source region and a drain region, wherein the lower layer of the interlayer insulator is used as an etching stopper;

forming a second contact hole overlapped with the first contact hole through the interlayer insulator to reach at least one of the source region and the drain region;

forming a second conductive film;